



#### **General Description**

The WSD100N15DN56G is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD100N15DN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

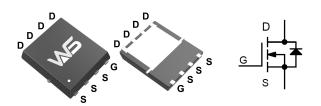
#### **Product Summery**

BVDSS	RDSON	ID
150V	9mΩ	100A

# **Applications**

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System

# **DFN5X6-8L Pin Configuration**



#### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
V <sub>DS</sub>	Drain-Source Voltage	150	V	
$V_{GS}$	Gate-Source Voltage	±20	V	
I <sub>D</sub>	Continuous Drain Current, V <sub>GS</sub> @ 10V(T <sub>C</sub> =25 ℃)	100	Α	
I <sub>DM</sub>	Pulsed Drain Current	360	Α	
EAS	Single Pulse Avalanche Energy	400	mJ	
P <sub>D</sub>	Total Power Dissipation <sub>C</sub> =25 <sup>C</sup> )	160	W	
RθJA	Thermal resistance, junction-ambient	62	°C/W	
RθJC	Thermal resistance, junction-case	0.78	°C/W	
T <sub>STG</sub>	Storage Temperature Range -55 to 175		$^{\circ}$	
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 175	${\mathbb C}$	



# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	150			V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =20A		9	12	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250uA$	2.0	3.0	4.0	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V , V <sub>GS</sub> =0V , T <sub>J</sub> =25℃			1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$			±100	nA
Qg	Total Gate Charge			66		
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =50V , V <sub>GS</sub> =10V , I <sub>D</sub> =20A		26		nC
$Q_{gd}$	Gate-Drain Charge			18		
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =50V ,		37		
Tr	Rise Time	V <sub>GS</sub> =10V		98		
T <sub>d(off)</sub>	Turn-Off Delay Time	$R_G=2\Omega$ ,		55		ns
T <sub>f</sub>	Fall Time	I <sub>D</sub> =20A		20		
C <sub>iss</sub>	Input Capacitance			5450		
Coss	Output Capacitance	V <sub>DS</sub> =30V , V <sub>GS</sub> =0V , f=1MHz		1730		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			195		

### **Diode Characteristics**

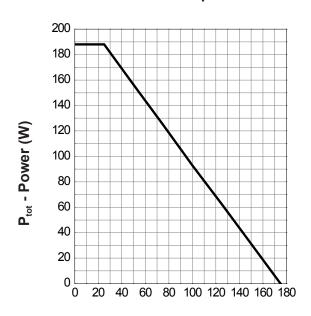
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V =V =0V Force Current			100	Α
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			360	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =20A , T <sub>J</sub> =25℃			1.3	V

# ■ Note

- <sup>1</sup>) Repetitive rating; pulse width limited by max. junction temperature.
- $^{2}$  ) Pd is based on max. junction temperature, using junction-case thermal resistance.
- $^3$  ) The value of R0JA is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 °C.
- $^4$  ) VDD=50 V, RG=25 $\Omega$ , L=0.5 mH, starting Tj=25 °C.
- <sup>5</sup> ) Calculated continuous current based on maximum allowable junction temperature.

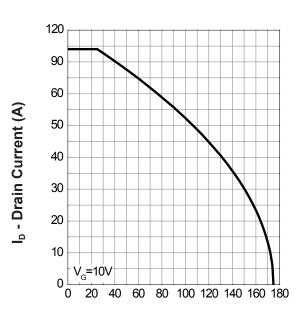


# Power Dissipation



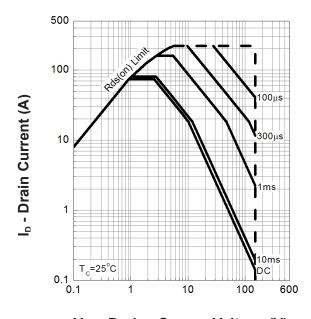
T<sub>c</sub> - Case Temperature (°C)

#### **Drain Current**



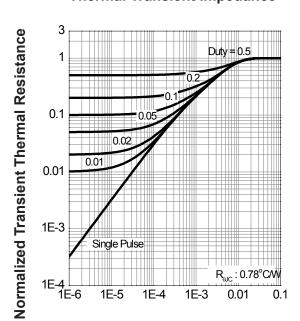
T<sub>c</sub> - Case Temperature (°C)

# **Safe Operation Area**



V<sub>DS</sub> - Drain - Source Voltage (V)

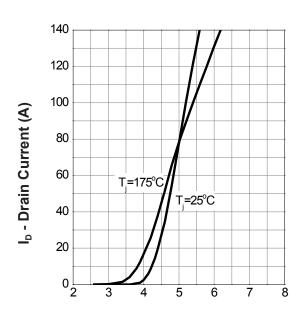
# **Thermal Transient Impedance**



**Square Wave Pulse Duration (sec)** 

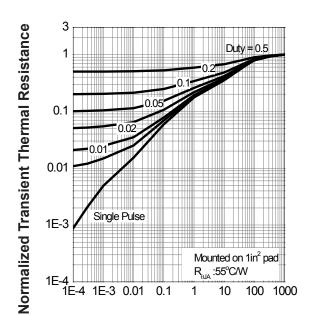


#### **Transfer Characteristics**



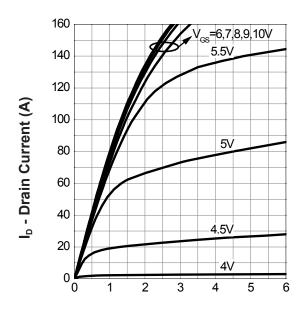
V<sub>GS</sub> - Gate-Source Voltage (V)

### **Thermal Transient Impedance**



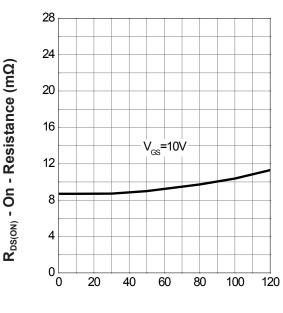
**Square Wave Pulse Duration (sec)** 

# **Output Characteristics**



V<sub>DS</sub> - Drain - Source Voltage (V)

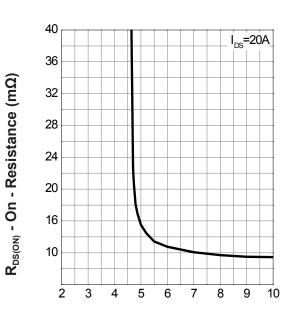
#### **Drain-Source On Resistance**



I<sub>D</sub> - Drain Current (A)

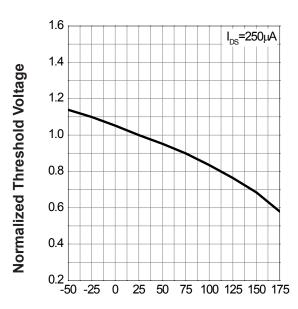


# **Gate-Source On Resistance**



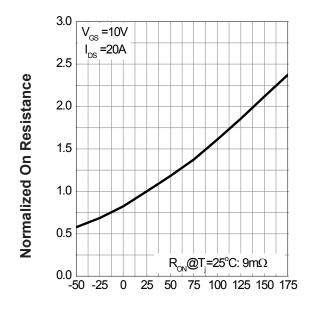
V<sub>GS</sub> - Gate - Source Voltage (V)

#### **Gate Threshold Voltage**



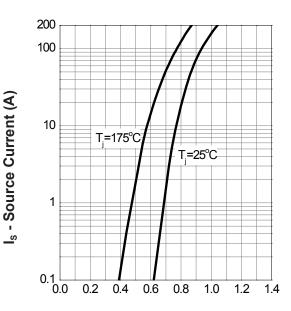
T<sub>j</sub> - Junction Temperature (°C)

# **Drain-Source On Resistance**



T<sub>j</sub> - Junction Temperature (°C)

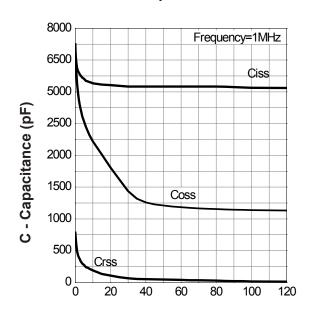
# Source-Drain Diode Forward



V<sub>SD</sub> - Source - Drain Voltage (V)

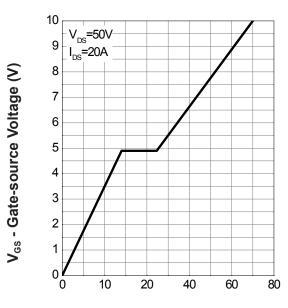


# Capacitance



V<sub>DS</sub> - Drain-Source Voltage (V)

# **Gate Charge**



Q<sub>G</sub> - Gate Charge (nC)



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